Shinjiro Hara

List of Publications by Year
in descending order

92 papers	3,239 citations	236925 25 h-index	161849 54 g-index
95 all docs	95 docs citations	95 times ranked	2375 citing authors

#	Article	IF	Citations
1	Tailoring Magnetic Domains and Magnetization Switching in CoFe Nanolayer Patterns with Their Thickness and Aspect Ratio on GaAs (001) Substrate. Physica Status Solidi (B): Basic Research, 2022, 259, .	1.5	2
2	Nanowire Field-Effect Transistors. , 2021, , 371-431.		2
3	Anomalous Angle-Dependent Magnetotransport Properties of Single InAs Nanowires. Nano Letters, 2020, 20, 618-624.	9.1	7
4	The transport properties of InAs nanowires: an introduction to MnAs/InAs heterojunction nanowires for spintronics. Journal Physics D: Applied Physics, 2020, 53, 333002.	2.8	4
5	Magnetization switching depending on magnetic fields applied to ferromagnetic MnAs nanodisks selectively-grown on Si (111) substrates. AIP Advances, 2020, 10, 125003.	1.3	0
6	Magnetization characterization of MnAs nanoclusters at close range in bended MnAs/InAs heterojunction nanowires. Journal of Crystal Growth, 2019, 507, 241-245.	1.5	8
7	Selective-area growth of magnetic MnAs nanodisks on Si (1â€¯1â€¯1) substrates using multiple types of dielectric masks. Journal of Crystal Growth, 2019, 507, 226-231.	1.5	1
8	Selective-area growth and transport properties of MnAs/InAs heterojunction nanowires. Journal of Materials Research, 2019, 34, 3863-3876.	2.6	7
9	Magnetic domain structure and domain wall analysis of ferromagnetic MnAs nanodisks selectively-grown on Si (111) substrates for spintronic applications. Journal of Applied Physics, 2018, 124, .	2.5	3
10	Analyses of magnetization switching and magnetic domains in lateral MnAs nanowires in combination with structural characterization. Japanese Journal of Applied Physics, 2017, 56, 06GH05.	1.5	3
11	Magnetization in vertical MnAs/InAs heterojunction nanowires. Journal of Crystal Growth, 2017, 464, 80-85.	1.5	9
12	Single-photon emission from InAsP quantum dots embedded in density-controlled InP nanowires. Japanese Journal of Applied Physics, 2017, 56, 04CP04.	1.5	14
13	Shape control of ferromagnetic MnAs nanoclusters exhibiting magnetization switching in vertical MnAs/InAs heterojunction nanowires. Japanese Journal of Applied Physics, 2017, 56, 06GH03.	1.5	5
14	Synthesis and structural characterization of vertical ferromagnetic MnAs/semiconducting InAs heterojunction nanowires. Japanese Journal of Applied Physics, 2016, 55, 075503.	1.5	10
15	NaDev: An Annotated Corpus to Support Information Extraction from Research Papers on Nanocrystal Devices. Journal of Information Processing, 2016, 24, 554-564.	0.4	1
16	Selective-area growth and magnetic characterization of MnAs/AlGaAs nanoclusters on insulating Al2O3 layers crystallized on Si(111) substrates. Applied Physics Letters, 2016, 108, 043108.	3.3	5
17	Selectiveâ€area growth and magnetic reversals of ferromagnetic nanoclusters on semiconducting substrate for magnetic logic applications (Phys. Status Solidi B 9/2015). Physica Status Solidi (B): Basic Research, 2015, 252, .	1.5	0
18	Analysis of magnetic random telegraph noise in individual arrangements of a small number of coupled MnAs nanoclusters. Physical Review B, 2015, 92, .	3.2	3

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19	Selectiveâ€area growth and magnetic reversals of ferromagnetic nanoclusters on semiconducting substrate for magnetic logic applications. Physica Status Solidi (B): Basic Research, 2015, 252, 1925-1933.	1.5	7
20	Framework for automatic information extraction from research papers on nanocrystal devices. Beilstein Journal of Nanotechnology, 2015, 6, 1872-1882.	2.8	9
21	Selective-area growth and magnetic characterization of lateral MnAs nanowires. Journal of Crystal Growth, 2015, 414, 151-155.	1.5	4
22	Magnetoresistance effects and spin-valve like behavior of an arrangement of two MnAs nanoclusters. Applied Physics Letters, 2015, 106, .	3.3	9
23	Growth of AlGaAs nanostructures on crystallized Al2O3interlayers for semiconducting nanowire growth on glass substrate. Japanese Journal of Applied Physics, 2015, 54, 075504.	1.5	2
24	Compositionâ€"dependent growth dynamics of selectively grown InGaAs nanowires. Materials Research Express, 2014, 1, 015036.	1.6	4
25	Transport Properties of Hybrids with Ferromagnetic MnAs Nanoclusters and Their Potential for New Magnetoelectronic Devices. Advanced Materials, 2014, 26, 8079-8095.	21.0	26
26	Selective-Area Growth of InAs Nanowires with Metal/Dielectric Composite Mask and Their Application to Vertical Surrounding-Gate Field-Effect Transistors. Applied Physics Express, 2013, 6, 045001.	2.4	7
27	Pitch-Independent Realization of 30-nm-Diameter InGaAs Nanowire Arrays by Two-Step Growth Method in Selective-Area Metalorganic Vapor-Phase Epitaxy. Applied Physics Express, 2013, 6, 025502.	2.4	15
28	Difference in formation of ferromagnetic MnAs nanoclusters on III-V semiconducting nanowire templates. , 2013, , .		4
29	Growth and Characterization of MnAs Nanoclusters Embedded in GaAs Nanowires by Metalâ€"Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH01.	1.5	6
30	Automatic Information Extraction of Experiments from Nanodevices Development Papers. , 2012, , .		4
31	Fabrication and Characterization of InP Nanowire Light-Emitting Diodes. Japanese Journal of Applied Physics, 2012, 51, 02BN03.	1.5	9
32	Influence of growth temperature on growth of InGaAs nanowires in selective-area metalâ€"organic vapor-phase epitaxy. Journal of Crystal Growth, 2012, 338, 47-51.	1.5	22
33	Fabrication of Axial and Radial Heterostructures for Semiconductor Nanowires by Using Selective-Area Metal-Organic Vapor-Phase Epitaxy. Journal of Nanotechnology, 2012, 2012, 1-29.	3.4	19
34	Selective-Area Growth and Electrical Characterization of Hybrid Structures between Semiconducting GaAs Nanowires and Ferromagnetic MnAs Nanoclusters. Japanese Journal of Applied Physics, 2012, 51, 11PE01.	1.5	3
35	Growth and Characterization of MnAs Nanoclusters Embedded in GaAs Nanowires by Metalâ€"Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH01.	1.5	10
36	Selective-Area Growth and Electrical Characterization of Hybrid Structures between Semiconducting GaAs Nanowires and Ferromagnetic MnAs Nanoclusters. Japanese Journal of Applied Physics, 2012, 51, 11PE01.	1.5	8

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37	IIIâ€"V Nanowires on Si Substrate: Selective-Area Growth and Device Applications. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1112-1129.	2.9	145
38	Lattice-mismatched InGaAs nanowires formed on GaAs(1 1 1)B by selective-area MOVPE. Journal of Crystal Growth, 2011, 315, 148-151.	1.5	12
39	Ferromagnetic MnAs Nanocluster Composites Position-Controlled on GaAs (111)B Substrates toward Lateral Magnetoresistive Devices. Japanese Journal of Applied Physics, 2011, 50, 06GH01.	1.5	6
40	Influence of ordered arrangements of cluster chains on the hopping transport in GaAs:Mn/MnAs hybrids at low temperatures. Physical Review B, 2011, 83, .	3.2	18
41	Effect of the cluster magnetization on the magnetotransport at low temperatures in ordered arrays of MnAs nanoclusters on (111)<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>B</mml:mi></mml:math>GaAs. Physical Review B, 2011, 84, .	3.2	16
42	Selective-area growth of III-V nanowires and their applications. Journal of Materials Research, 2011, 26, 2127-2141.	2.6	109
43	Growth and Characterization of a GaAs Quantum Well Buried in GaAsP/GaAs Vertical Heterostructure Nanowires by Selective-Area Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 04DH03.	1.5	4
44	Construction of tagged corpus for Nanodevices development papers. , 2011, , .		3
45	Growth and Characterization of a GaAs Quantum Well Buried in GaAsP/GaAs Vertical Heterostructure Nanowires by Selective-Area Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 04DH03.	1.5	2
46	Ferromagnetic MnAs Nanocluster Composites Position-Controlled on GaAs (111)B Substrates toward Lateral Magnetoresistive Devices. Japanese Journal of Applied Physics, 2011, 50, 06GH01.	1.5	6
47	Magnetic Sensor Devices Based on Ordered Planar Arrangements of MnAs Nanocluster. IEEE Transactions on Magnetics, 2010, 46, 1702-1704.	2.1	13
48	Fabrication and characterization of GaAs quantum well buried in AlGaAs/GaAs heterostructure nanowires. Journal of Crystal Growth, 2010, 312, 3592-3598.	1.5	15
49	Comparison of the magnetic properties of GaInAs/MnAs and GaAs/MnAs hybrids with random and ordered arrangements of MnAs nanoclusters. Journal of Applied Physics, 2010, 107, 013701.	2.5	22
50	Growth and Characterization of InGaAs Nanowires Formed on GaAs(111)B by Selective-Area Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2010, 49, 04DH08.	1.5	29
51	Vertical Surrounding Gate Transistors Using Single InAs Nanowires Grown on Si Substrates. Applied Physics Express, 2010, 3, 025003.	2.4	80
52	GaAs/AlGaAs Core Multishell Nanowire-Based Light-Emitting Diodes on Si. Nano Letters, 2010, 10, 1639-1644.	9.1	305
53	Structural Transition in Indium Phosphide Nanowires. Nano Letters, 2010, 10, 1699-1703.	9.1	108
54	Fabrication of III-V semicondctor nanowires by SA-MOVPE and their applications to photonic and photovoltaic devices. , 2010, , .		0

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55	Selective-area MOVPE growth and optical properties of single InAsP quantum dots embedded in InP NWs. , 2010, , .		1
56	Magnetic domain characterizations of anisotropic-shaped MnAs nanoclusters position-controlled by selective-area metal-organic vapor phase epitaxy. Applied Physics Letters, 2009, 94, 243117.	3.3	18
57	Growth Direction Control of Ferromagnetic MnAs Grown by Selective-Area Metalâ€“Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2009, 48, 04C137.	1.5	15
58	Analysis of twin defects in GaAs nanowires and tetrahedra and their correlation to GaAs(111)B surface reconstructions in selective-area metal organic vapour-phase epitaxy. Journal of Crystal Growth, 2009, 312, 52-57.	1.5	41
59	Single GaAs/GaAsP Coaxial Coreâ^'Shell Nanowire Lasers. Nano Letters, 2009, 9, 112-116.	9.1	254
60	Selective-area growth of vertically aligned GaAs and GaAs/AlGaAs coreâ€“shell nanowires on Si(111) substrate. Nanotechnology, 2009, 20, 145302.	2.6	145
61	Self-assembly and selective-area formation of ferromagnetic MnAs nanoclusters on lattice-mismatched semiconductor surfaces by MOVPE. Journal of Crystal Growth, 2008, 310, 2390-2394.	1.5	29
62	Growth of InGaAs nanowires by selective-area metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2008, 310, 2359-2364.	1.5	49
63	SA-MOVPE of InGaAs nanowires and their compositions studied by micro-PL measurement. Journal of Crystal Growth, 2008, 310, 5111-5113.	1.5	24
64	Control of InAs Nanowire Growth Directions on Si. Nano Letters, 2008, 8, 3475-3480.	9.1	320
65	Growth characteristics of GaAs nanowires obtained by selective area metalâ€“organic vapour-phase epitaxy. Nanotechnology, 2008, 19, 265604.	2.6	94
66	Formation of InP and InGaAs Air-Hole Arrays on InP(111) Substrates by Selective-Area Metalâ€“Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2008, 47, 3354-3358.	1.5	0
67	Metalâ€“Organic Vapor Phase Epitaxial Growth Condition Dependences of MnAs Nanocluster Formation on GaInAs (111)A Surfaces. Japanese Journal of Applied Physics, 2008, 47, 3253-3256.	1.5	7
68	Characterization of Fabry-PÃ©rot microcavity modes in GaAs nanowires fabricated by selective-area metal organic vapor phase epitaxy. Applied Physics Letters, 2007, 91, 131112.	3.3	59
69	Electrical Characterizations of InGaAs Nanowire-Top-Gate Field-Effect Transistors by Selective-Area Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 7562.	1.5	45
70	Crystallographic Structure of InAs Nanowires Studied by Transmission Electron Microscopy. Japanese Journal of Applied Physics, 2007, 46, L1102-L1104.	1.5	53
71	Observation of Microcavity Modes and Waveguides in InP Nanowires Fabricated by Selective-Area Metalorganic Vapor-Phase Epitaxy. Nano Letters, 2007, 7, 3598-3602.	9.1	62
72	Magnetic properties of hexagonal MnAs nanoclusters formed on GaInAs (111) surfaces by metal-organic vapor phase epitaxy. Journal of Magnetism and Magnetic Materials, 2007, 310, e833-e835.	2.3	3

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73	Self-assembled formation of ferromagnetic MnAs nanoclusters on GaInAs/InP (111) B layers by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2007, 298, 612-615.	1.5	13
74	Mechanism of catalyst-free growth of GaAs nanowires by selective area MOVPE. Journal of Crystal Growth, 2007, 298, 616-619.	1.5	135
75	Growth of highly uniform InAs nanowire arrays by selective-area MOVPE. Journal of Crystal Growth, 2007, 298, 644-647.	1.5	123
76	Optical activity of a single MnAs cluster: Birefringence or Kerr effect. Journal of Magnetism and Magnetic Materials, 2006, 301, 478-488.	2.3	2
77	Hexagonal ferromagnetic MnAs nanocluster formation on GaInAsâˆ•InP (111)B layers by metal-organic vapor phase epitaxy. Applied Physics Letters, 2006, 89, 113111.	3.3	27
78	Catalyst-free growth of semiconductor nanowires by selective area MOVPE. AIP Conference Proceedings, 2005, , .	0.4	1
79	Ferromagnetic nanoclusters hybridized in Mn-incorporated GaInAs layers during metalâ€"organic vapour phase epitaxial growth on InP layers under low growth temperature conditions. Nanotechnology, 2005, 16, 957-965.	2.6	17
80	Fabrication and characterization of freestanding GaAsâˆ•AlGaAs core-shell nanowires and AlGaAs nanotubes by using selective-area metalorganic vapor phase epitaxy. Applied Physics Letters, 2005, 87, 093109.	3.3	168
81	Cluster formation and magnetic properties of Mn-incorporated (GaIn)As/InP layers grown by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2004, 261, 330-335.	1.5	14
82	Optical characterization and laser operation of InGaAs quantum wires on GaAs multiatomic steps. Solid-State Electronics, 1998, 42, 1233-1238.	1.4	12
83	Self-organised InGaAs quantum wire lasers on GaAs multi-atomic steps. Electronics Letters, 1998, 34, 894.	1.0	28
84	A Novel Electron Wave Interference Device Using Multiatomic Steps on Vicinal GaAs Surfaces Grown by Metalorganic Vapor Phase Epitaxy: Investigation of Transport Properties. Japanese Journal of Applied Physics, 1997, 36, 1966-1971.	1.5	6
85	Formation and characterization of InGaAs strained quantum wires on GaAs multiatomic steps grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 1997, 170, 579-584.	1.5	21
86	Theoretical and experimental investigation of an electron interference device using multiatomic steps on vicinal GaAs surfaces. Physica B: Condensed Matter, 1996, 227, 295-298.	2.7	5
87	Multiatomic step formation on GaAs(001) vicinal surfaces during thermal treatment. Journal of Crystal Growth, 1996, 160, 235-240.	1.5	18
88	Multiatomic step formation mechanism of metalorganic vapor phase epitaxial grown GaAs vicinal surfaces and its application to quantum well wires. Journal of Crystal Growth, 1995, 146, 183-187.	1.5	27
89	Quantum Well Wire Fabrication Method Using Self-Organized Multiatomic Steps on Vicinal (001) GaAs Surfaces by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1995, 34, 4401-4404.	1.5	36
90	Formation and photoluminescence characterization of quantum well wires using multiatomic steps grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 1994, 145, 692-697.	1.5	36

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91	Growth of Coreâ€“Shell InP Nanowires for Photovoltaic Application by Selective-Area Metal Organic Vapor Phase Epitaxy. Applied Physics Express, 0, 2, 035004.	2.4	185
92	Bottom-Up Formation of Vertical Free-Standing Semiconductor Nanowires Hybridized with Ferromagnetic Nanoclusters. Materials Science Forum, 0, 783-786, 1990-1995.	0.3	1